

# CD4093B Types

## CMOS Quad 2-Input NAND Schmitt Triggers

High-Voltage Types (20 Volt Rating)

■ CD4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive- and negative-going signals. The difference between the positive voltage ( $V_p$ ) and the negative voltage ( $V_N$ ) is defined as hysteresis voltage ( $V_H$ ) (see Fig. 2).

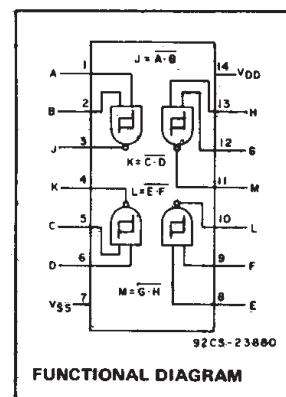
The CD4093B types are supplied in 14-lead hermetic dual-in-line ceramic packages (F3A suffix), 14-lead dual-in-line plastic packages (E suffix), 14-lead small-outline packages (M, MT, M96, and NSR suffixes), and 14-lead thin shrink small-outline packages (PW and PWR suffixes).

### Features:

- Schmitt-trigger action on each input with no external components
- Hysteresis voltage typically 0.9 V at  $V_{DD} = 5$  V and 2.3 V at  $V_{DD} = 10$  V
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1  $\mu$ A at 18 V over full package-temperature range, 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

### Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators
- NAND logic

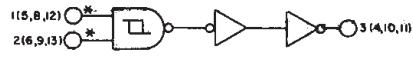


FUNCTIONAL DIAGRAM

### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range ( $T_A$ = Full Package Temp. Range)	3	18	V



\* ALL INPUTS PROTECTED BY CMOS  
PROTECTION NETWORK

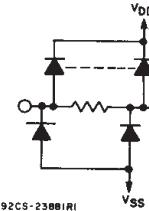


Fig. 1 – Logic diagram—1 of 4 Schmitt triggers.

### MAXIMUM RATINGS, Absolute-Maximum Values:

#### DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )

Voltages referenced to  $V_{SS}$  Terminal) ..... -0.5V to +20V

#### INPUT VOLTAGE RANGE, ALL INPUTS

-0.5V to  $V_{DD}$  +0.5V

#### DC INPUT CURRENT, ANY ONE INPUT

$\pm 10$ mA

#### PACKAGE THERMAL IMPEDANCE, $\theta_{JA}$ (See Note 1):

E package ..... 80°C/W

M package ..... 86°C/W

NS package ..... 76°C/W

#### DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR  $T_A$  = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100mW

OPERATING-TEMPERATURE RANGE ( $T_A$ ) ..... -55°C to +125°C

STORAGE TEMPERATURE RANGE ( $T_{stg}$ ) ..... -65°C to +150°C

#### LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16  $\pm$  1/32 inch (1.59  $\pm$  0.79mm) from case for 10s max ..... +265°C

NOTE 1: Package thermal impedance is calculated in accordance with JESD 51-7.

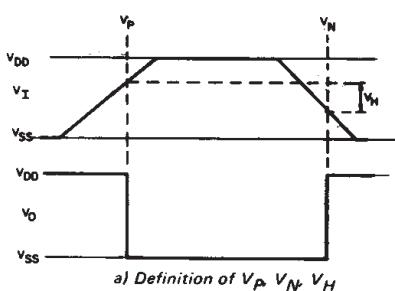
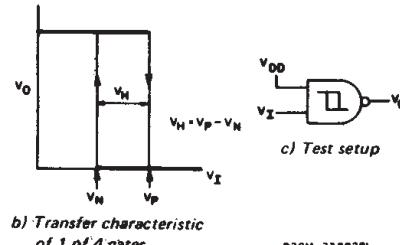


Fig. 2 – Hysteresis definition, characteristic, and test setup.



b) Transfer characteristic  
of 1 of 4 gates.

c) Test setup

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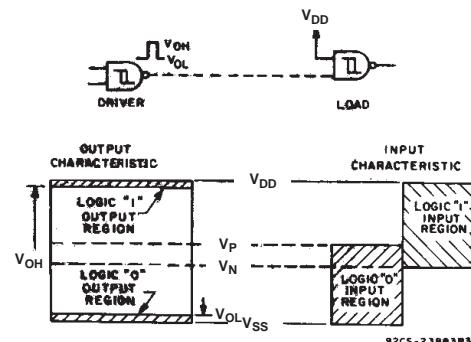


Fig. 3 – Input and output characteristics.